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# PCN # 167 Notification Date: 4 April 2019

## **Product / Process Change Notice**

#### Parts Affected:

Chip process, CP373, N-channel mosfets, wafers and bare die.

#### **Extent of Change:**

The CP373 wafer process has been discontinued and is being replaced with the CP398X wafer process. See figures 1 and 2 for details.

#### Reason for Change:

The CP373 wafer process has been replaced in order to enhance the manufacturing process controls and device performance. In addition, this change is being made to ensure undisrupted future supply of product.

#### **Effect of Change:**

The wafer process meets all electrical specifications of the individual devices listed on the following page.

#### **Qualification:**

P/N: CP398X Chip Process Package: SOIC-8

No.		Test	Conditions (Reference standards are in bold)	Qty	Pass/Fail	Test Results	
1		Device Life Tests					
	а	High Temperature Gate Bias (HTGB)	T=150°C, t = 1000 hours 100% V_GS JESD22-A108	80	Pass	80/80	
	b	High Temperature Reverse Bias (HTRB)	T=150°C, t = 1000 hours 80% V_DS JESD22-A108	80	Pass	80/80	

#### **Effective Date of Change:**

Existing inventory of chip process CP373 will be shipped until depleted.

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### **Sample Availability:**

Please contact your salesperson or manufacturer's representative for samples.

Figure 1: CP373 Chip Geometry (Discontinued)

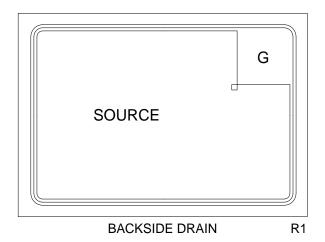
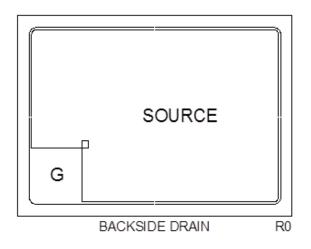


Figure 2: CP398X Chip Geometry



Wafer Diameter: 8 inch
Die Size: 39 x 27 mils
Die Thickness: 7.5 mils
Bond Pad Size (Gate): 6.5 x 6.5 mils
Bond Pad Size (Source): 33 x 21 mils
Topside Metal: Al (40,000Å)

Backside Metal: Ti/Ni/Ag (1000Å/3000Å/10000Å)

Wafer Diameter: 8 inch
Die Size: 37.8 x 26 mils
Die Thickness: 5.5 mils
Bond Pad Size (Gate): 7.3 x 7.3 mils
Bond Pad Size (Source): 34 x 22.2 mils
Topside Metal: Al-Cu (40,000Å)

Backside Metal: Ti/Ni/Ag (1000Å/3000Å/10000Å)

### **Part Numbers Affected:**

CEN1233	CP373-CMPDM303NH-CT
	CP373-CMPDM303NH-CT
	CP373-CTLDM303N-WN
	CTLDM303N-M832DS

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As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	

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